

# AG202-86

InGaP HBT Gain Block

Product Information



wj

## Product Features

- DC – 6000 MHz
- +7.5 dBm P1dB at 900 MHz
- +19.5 dBm OIP3 at 900 MHz
- 15 dB Gain at 900 MHz
- Single Voltage Supply
- Green SOT-86 SMT Package
- Internally matched to 50 Ω

## Applications

- Mobile Infrastructure
- CATV / DBS
- W-LAN / ISM
- RFID
- Defense / Homeland Security
- Fixed Wireless

## Product Description

The AG202-86 is a general-purpose buffer amplifier that offers high dynamic range in a low-cost surface-mount package. At 900 MHz, the AG202-86 typically provides 15 dB gain, +19.5 dBm OIP3, and +7.5 dBm P1dB. The device combines dependable performance with consistent quality to maintain MTTF values exceeding 100 years at mounting temperatures of +85 °C & is housed in a SOT-86 (micro-X) industry-standard SMT lead-free/green/RoHS compliant package.

The AG202-86 consists of Darlington pair amplifiers using the high reliability InGaP/GaAs HBT process technology and only requires DC-blocking capacitors, a resistor, and an inductive RF choke for operation.

The broadband MMIC amplifier can be directly applied to various current and next generation wireless technologies such as GPRS, GSM, CDMA, and W-CDMA. In addition, the AG202-86 will work for other various applications within the DC to 6 GHz frequency range such as CATV and fixed wireless.

## Functional Diagram



Function	Pin No.
Input	1
Output/Bias	3
Ground	2, 4

## Specifications <sup>(1)</sup>

Parameter	Units	Min	Typ
Operational Bandwidth	MHz	DC	6000
Test Frequency	MHz	900	900
Gain	dB		15
Input Return Loss	dB		16
Output Return Loss	dB		16
Output IP3 <sup>(2)</sup>	dBm	+19.6	+19.5
Output IP2	dBm	+27	+27
Output P1dB	dBm	+7.5	+7.5
Noise Figure	dB		3.5
Test Frequency	MHz	900	900
Gain	dB	12.9	13.9
Output IP3 <sup>(2)</sup>	dBm	+19	+19
Output P1dB	dBm	+7	+7
Device Voltage	V	+4.5	+4.5
Device Current	mA	±0	±0

1. Test conditions: 25° C, Supply Voltage = +5 V, Z<sub>in</sub> = 47.5 Ω, Z<sub>out</sub> = 50 Ω.  
 2. 3OIP measured with two tones at an output power of 10 dBm/tones separated by 10 MHz. The suppression on the lowest frequency product is 10 dB. Calculated 3OIP using a 2:1 rule.

## Typical Performance <sup>(1)</sup>

Parameter	Units	Typical
Operational Bandwidth	MHz	500, 900, 1900, 2140
Gain	dB	15.0, 14.7, 13.9, 13.5
Input Return Loss	dB	-25, -25, -20, -16
Output Return Loss	dB	-16, -16, -16, -12
Output P1dB	dBm	+7.7, +7.6, +6.5, +6.2
Output IP3	dBm	+19.9, +19.6, +19.2, +18.9
Noise Figure	dB	3.5, 3.5, 3.8, 3.8

## Absolute Maximum Rating

Parameter	Rating
Operating Case Temperature	-40 to +85 °C
Storage Temperature	-55 to +125 °C
DC Voltage	+4.5 V
RF Output Power (continuous)	+10 dBm
Maximum Temperature	+250° C

Operation of this device above any of these parameters may cause permanent damage.

## Ordering Information

Part No.	Description
AG202-86	InGaP HBT Gain Block (lead-tin SOT-86 Pkg)
AG202-86G	InGaP HBT Gain Block (lead-free/green/RoHS-compliant SOT-86 Pkg)

Specifications and information are subject to change without notice

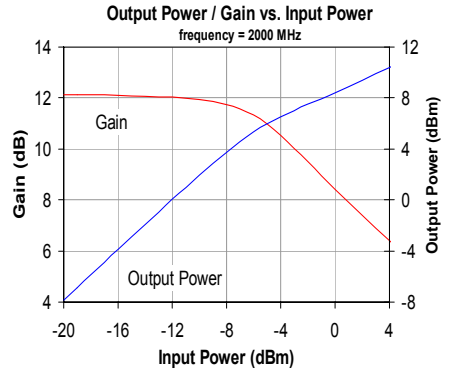
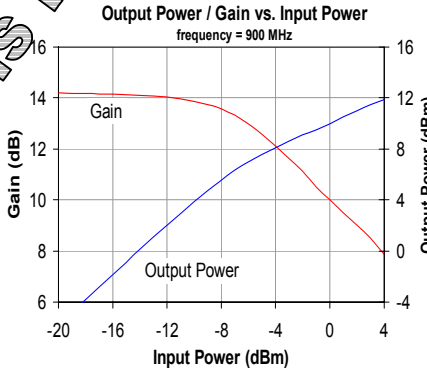
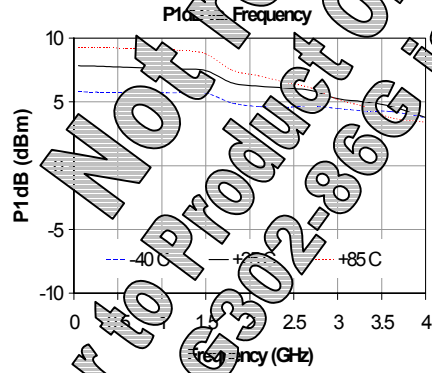
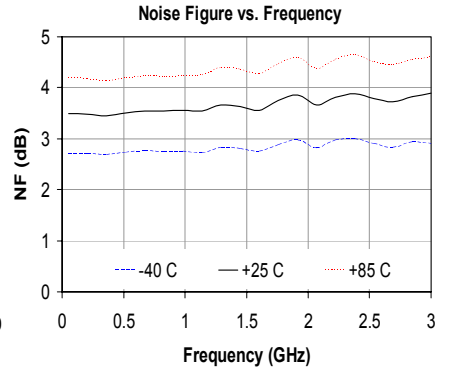
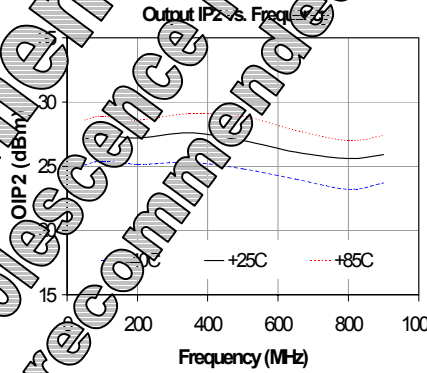
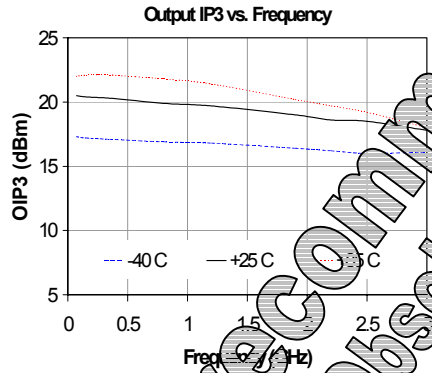
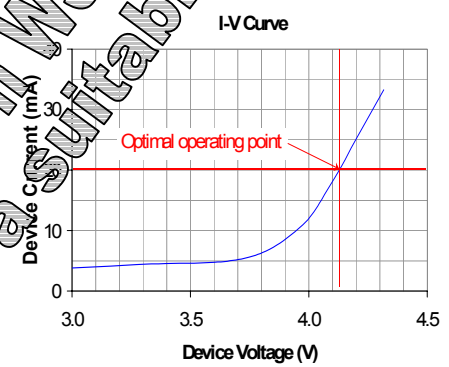
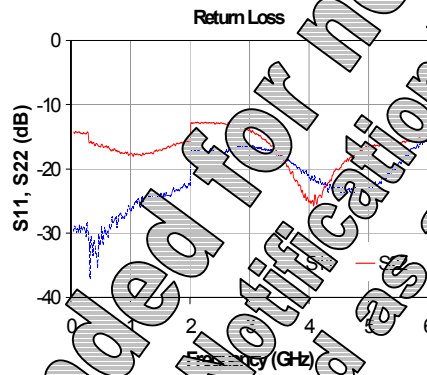
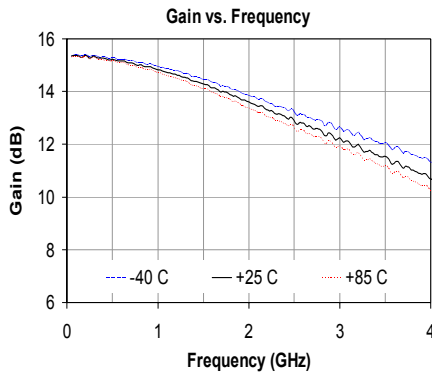


### Typical Device RF Performance

Supply Bias = +5 V,  $R_{bias} = 47.5 \Omega$ ,  $I_{cc} = 20 \text{ mA}$

Frequency	MHz	100	500	900	1900	2140	2400	3500	5800
S21	dB	15.0	15.0	14.7	13.9	13.5	13.3		
S11	dB	-25	-25	-25	-20	-16	-16		
S22	dB	-14	-16	-16	-16	-12	-12		
Output P1dB	dBm	+7.8	+7.7	+7.6	+6.5	+6.2	+6.0	+4.7	
Output IP3	dBm	+20.2	+19.9	+19.6	+19.2	+18.9			
Noise Figure	dB	3.5	3.5	3.5	3.8	3.8			

1. Test conditions: T = 25° C, Supply Voltage = +5 V, Device Voltage = 4.05 V,  $R_{bias} = 47.5 \Omega$ , I = 20 mA typical, 50  $\Omega$  System.
2. 3OIP measured with two tones at an output power of -10 dBm/tone separated by 10 MHz. The suppression on the largest IM3 product is used to calculate the 3OIP using a 2-tone rule.
3. Data is shown as device performance only. Actual implementation for the desired frequency band will be determined by external components shown in the application circuit.



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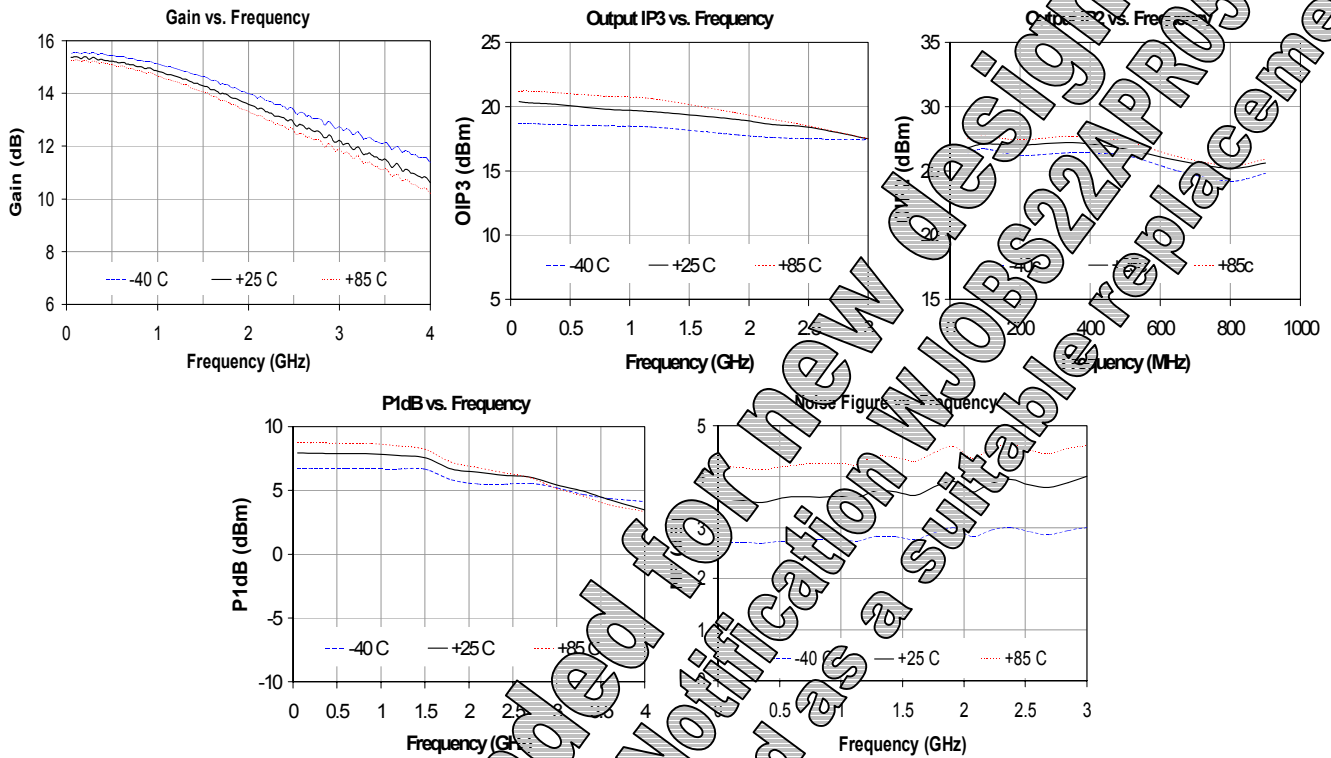
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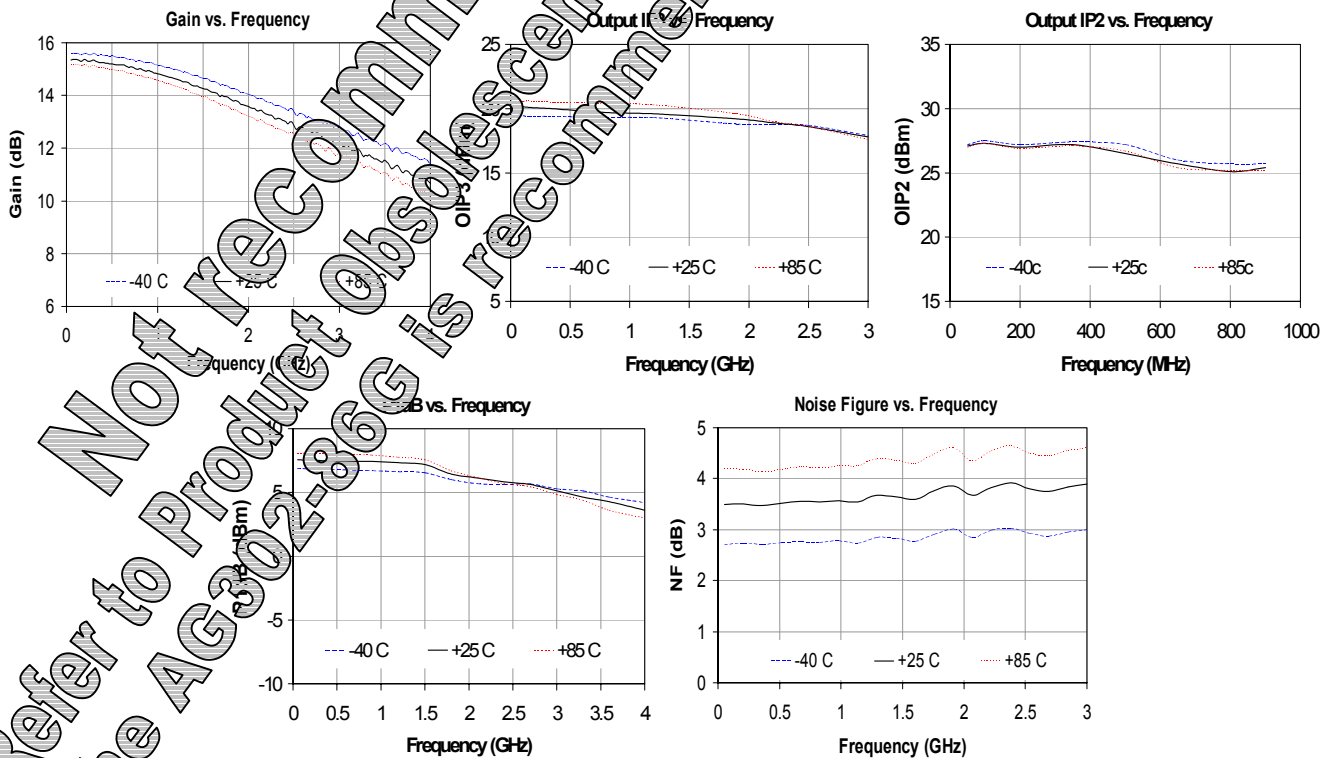
## Typical Device RF Performance (cont'd)

Supply Bias = +6 V,  $R_{bias} = 98 \Omega$ ,  $I_{cc} = 20 \text{ mA}$



## Typical Device RF Performance

Supply Bias = +6 V,  $R_{bias} = 198 \Omega$ ,  $I_{cc} = 20 \text{ mA}$



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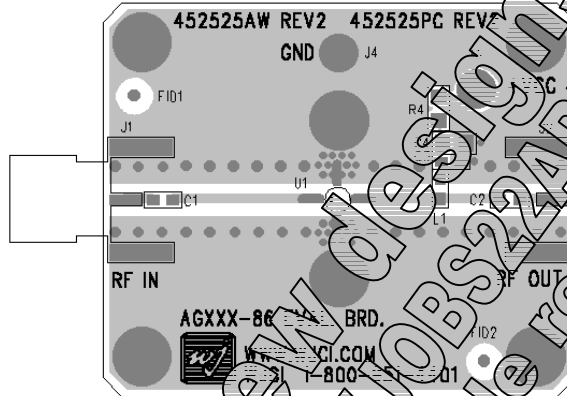
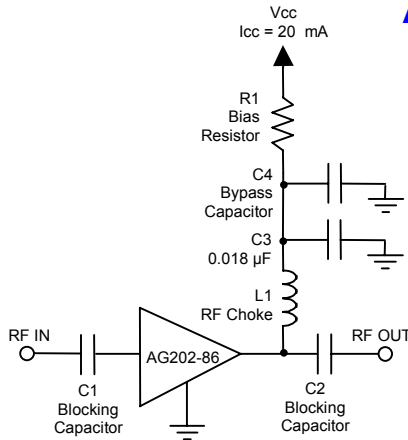
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Product Information



## Application Circuit



### Recommended Component Values

Reference Designator	Frequency (MHz)					
	50	500	900	1900	2200	3500
L1	820 nH	220 nH	68 nH	27 nH	22 nH	10 nH
C1, C2, C4	.018 µF	1000 pF	100 pF	68 pF	68 pF	68 pF

- The proper values for the components are dependent upon the intended frequency of operation.
- The following values are contained on the evaluation board to achieve optimal broadband performance.

Ref. Desig.	Value / Type
L1	39 nH wirewound inductor
C1, C2	56 pF chip capacitor
C3	0.018 µF chip capacitor
C4	Do Not Place
R1	47.5 Ω 1% tolerance

### Recommended Bias Resistor Values

Supply Voltage	R1 value	Size
5 V	47.5 ohms	0603
6 V	98 ohms	0603
7 V	148 ohms	0805
8 V	198 ohms	0805
9 V	248 ohms	1206
10 V	298 ohms	1210
12 V	398 ohms	1210

The proper value for R1 is dependent upon the supply voltage and allows for bias stability over temperature. WJ recommends a minimum supply bias of +5 V. A 1% tolerance resistor is recommended.

## Typical Device Data

S-Parameters ( $V_{device} = +4.05 V$ ,  $I_{cc} = 20 mA$ ,  $T = 25^\circ C$ , calibrated to device leads)

Freq (MHz)	S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
50	-29.48	1.00	17.85	-19.12	1.51	-14.31	-3.56	
250	-30.29	28.74	170.11	-19.61	0.95	-14.53	-8.85	
500	-31.03	87.51	160.10	-19.66	-3.57	-16.48	-19.17	
750	-27.59	86.84	150.47	-19.68	-6.17	-17.15	-32.28	
1000	-26.46	74.45	141.16	-19.90	-10.13	-17.58	-45.39	
1250	-26.66	66.11	131.45	-19.39	-8.85	-17.61	-60.92	
1500	-27.27	55.30	122.26	-19.43	-11.48	-17.06	-74.62	
1750	-27.27	43.36	113.06	-19.47	-12.13	-16.31	-85.09	
2000	-27.42	31.3	104.15	-19.35	-15.69	-15.46	-92.30	
2250	-17.21	1.02	13.71	96.18	-19.25	-17.05	-12.73	
2500	-17.37	-12.94	13.48	89.93	-19.39	-22.66	-12.93	
2750	-16.72	21.72	13.25	81.58	-18.81	-24.09	-13.24	
3000	-16.72	13.01	73.71	-18.87	-23.14	-13.91	-103.44	
3250	-17.13	12.78	66.09	-18.60	-24.00	-15.45	-107.37	
3500	-16.72	38.73	12.55	58.42	-18.47	-28.95	-17.85	
3750	-19.36	-38.12	12.30	50.78	-18.33	-31.75	-21.54	
4000	-21.13	-32.13	12.04	42.86	-18.04	-33.50	-25.15	
4250	-21.33	-22.58	11.82	35.34	-17.74	-37.34	-22.92	
4500	-14.16	11.49	27.87	-17.63	-40.46	-20.10	126.02	
4750	-15.62	-18.03	11.21	19.99	-17.45	-42.62	-17.92	
5000	-23.18	-30.26	10.97	12.68	-17.43	-47.82	-16.53	
5250	-21.41	-56.84	10.69	5.73	-17.35	-50.98	-16.25	
5500	-19.16	-76.72	10.40	-0.95	-17.11	-54.42	-15.87	
5750	-16.72	-91.91	10.19	-7.71	-16.87	-57.56	-15.49	
6000	-15.23	-100.12	9.94	-14.32	-16.72	-60.23	-15.19	

Device S-parameters are available for download off of the website at: <http://www.wj.com>

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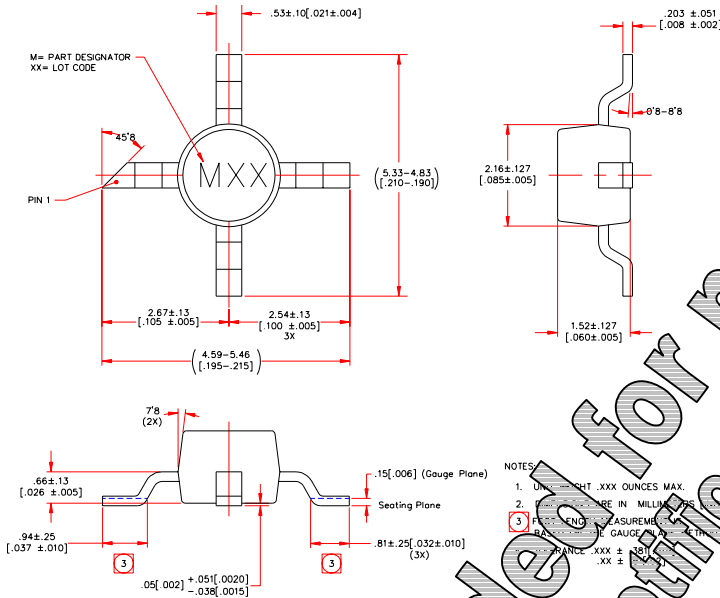
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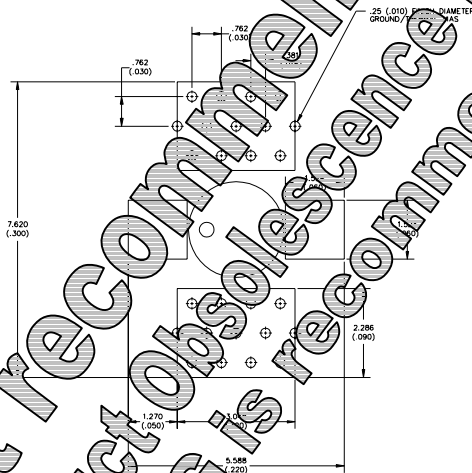
## AG202-86G (Green / Lead-free Sot-86 Package) Mechanical Information

This package is lead-free/Green/RoHS-compliant. It is compatible with both lead-free (maximum 260°C reflow temperature) and leaded (maximum 245°C reflow temperature) soldering processes. The plating material on the pins is annealed 99.99% pure copper.

### Outline Drawing



### Land Pattern



### The Specifications

Parameter	Rating
Operating Case Temperature	-40 to +85 °C
Thermal Resistance, R <sub>th</sub>	440 °C/W
Junction Temperature	121 °C

1. The thermal resistance is referenced from the hottest part of the device to the ground lead (pin 2 or 4).
2. The value corresponds to the typical biasing condition of +5V, 20 mA at an 85 °C case temperature. A minimum M<sub>0.1</sub> of 1 million hours is achieved for operation at temperatures below 177 °C.

### Pin Marking

The component will be marked with a "M" designator followed by a two digit numeric code on the top surface of the package.

Tape and reel specifications for this part are located on the website in the "Application Note" section.

### Moisture / ESD Rating

**Caution!** ESD sensitive device.

Moisture Rating: Class 1C  
 Value: Passes at 1000 V min.  
 Test: Human Body Model (HBM)  
 Standard: JEDEC Standard JESD22-A114

ESD Rating: Class IV  
 Value: Passes at 1000 V min.  
 Test: Charged Device Model (CDM)  
 Standard: JEDEC Standard JESD22-C101

MSL Rating: Level 3 at +260° C convection reflow  
 Standard: JEDEC Standard J-STD-020

### Mounting Config. Notes

1. Ground / thermal vias are critical for the proper performance of this device. Vias should use a .35mm (#80 / .0135") diameter drill and have a final plated thru diameter of .25 mm (.010").
2. Add as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.
3. Mounting screws can be added near the part to fasten the board to a heatsink. Ensure that the ground / thermal via region contacts the heatsink.
4. Do not put solder mask on the backside of the PC board in the region where the board contacts the heatsink.
5. RF trace width depends upon the PC board material and construction.
6. Use 1 oz. Copper minimum.
7. All dimensions are in millimeters (inches). Angles are in degrees.

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